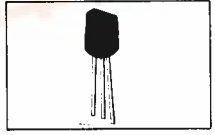




No. C268C



2SB598/2SD545

Silicon Epitaxial Planar Type Transistor
FOR AUDIO FREQUENCY POWER AMP., CONVERTERS,
ELECTRONIC GOVERNORS.

The 2SB598NP/2SD545NP are complementary pair transistors that are packaged in small packages and are large in current capacity and excellent in saturation characteristic and h_{FE} linearity. In addition to the above application areas, they are also suited for use in desk-top calculator power supplies, relay drivers.

Absolute Maximum Ratings/ $T_a = 25^\circ\text{C}$

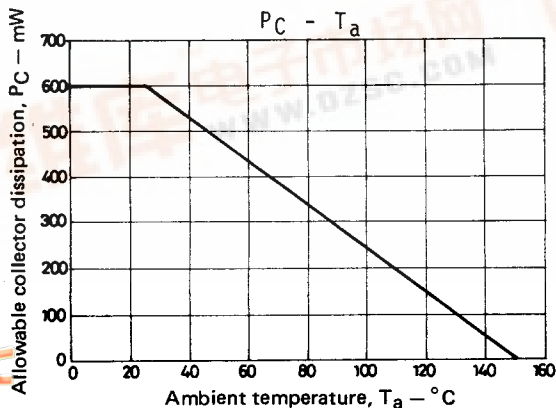
		2SB598	2SD545	unit
Collector to base voltage	V_{CBO}	-25	25	V
Collector to emitter voltage	V_{CEO}	-25	25	V
Emitter to base voltage	V_{EBO}	-5	5	V
Collector current	I_C	-1.0	1.0	A
	i_{cp}	-1.5	1.5	A
Collector dissipation	P_C	600	600	mW
Junction temperature	T_j	150	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 ~ +150	-55 ~ +150	$^\circ\text{C}$

Electrical Characteristics/ $T_a = 25^\circ\text{C}$

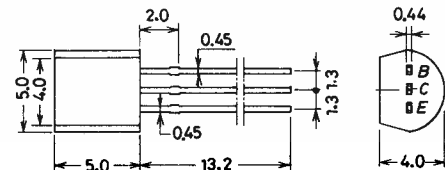
		2SB598			2SD545			unit
		min	typ	max	min	typ	max	
Collector cutoff current	I_{CBO} $V_{CB} = (-)20\text{V}, I_E = 0$			-1.0			1.0	μA
Emitter cutoff current	I_{EBO} $V_{EB} = (-)4\text{V}, I_C = 0$			-1.0			1.0	μA
Collector to base breakdown voltage	$V_{(BR)CBO}$ $I_C = (-)10\ \mu\text{A}, I_E = 0$	-25			25			V
Collector to emitter breakdown voltage	$V_{(BR)CEO}$ $I_C = (-)1\ \text{mA}, R_{BE} = \infty\ \Omega$	-25			25			V
Emitter to base breakdown voltage	$V_{(BR)EBO}$ $I_E = (-)10\ \mu\text{A}, I_C = 0$	-5			5			V
DC current gain	$h_{FE(1)}$ * $V_{CE} = (-)2\text{V}, I_C = (-)50\text{mA}$	60		560	60		560	
	$h_{FE(2)}$ $V_{CE} = (-)2\text{V}, I_C = (-)1\text{A(pulse)}$	30			30			
Gain bandwidth product	f_T $V_{CE} = (-)10\text{V}, I_C = (-)50\text{mA}$		180			180		MHz
Common base output capacitance	C_{ob} $V_{CB} = (-)10\text{V}, f = 1\ \text{MHz}$		25			15		pF
Collector to emitter saturation voltage	$V_{CE(sat)}$ $I_C = (-)500\text{mA}, I_B = (-)50\text{mA}$	-0.15	-0.5		0.1	0.3		V
Base to emitter saturation voltage	$V_{BE(sat)}$ $I_C = (-)500\text{mA}, I_B = (-)50\text{mA}$	-0.85	-1.2		0.85	1.2		V

* $h_{FE(1)}$ is classified by 2 V, 50 mA as follows:

60 D	120	100 E	200	160 F	320	280 G	560
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Case Outline 2003 (unit: mm)



JEDEC: TO-92
EIAJ: SC-43
SANYO: NP

B: Base
C: Collector
E: Emitter

